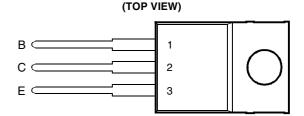
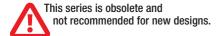
BOURNS®

- 40 W at 25°C Case Temperature
- 2 A Continuous Collector Current
- 3 A Peak Collector Current
- Typical t_f = 200 ns at 25°C



TO-220 PACKAGE



Pin 2 is in electrical contact with the mounting base.

MDTRACA

absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT
Collector-base voltage (I _E = 0)	V _{CBO}	1000	V
Collector-emitter voltage (V _{BE} = 0)	VCES	1000	V
Collector-emitter voltage (I _B = 0)	VCEO	450	V
Continuous collector current	I _C	2	Α
Peak collector current (see Note 1)	СМ	3	Α
Continuous device dissipation at (or below) 25°C case temperature	P _{tot}	40	W
Operating junction temperature range	T _j	-65 to +150	°C
Storage temperature range	T _{stg}	-65 to +150	°C

NOTE 1: This value applies for $t_p \le 2$ ms, duty cycle $\le 2\%$



electrical characteristics at 25°C case temperature (unless otherwise noted)

	TEST CONDITIONS					TYP	MAX	UNIT	
V _{CEO(sus)}	Collector-emitter sustaining voltage	I _C =	0.1 A	L = 25 mH	(see Note 2)	450			V
I _{CES}	Collector-emitter cut-off current	0_	1000 V 1000 V	$V_{BE} = 0$ $V_{BE} = 0$	T _C = 125°C			0.2 1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =	5 V	I _C = 0				1	mA
h _{FE}	Forward current transfer ratio	V _{CE} =	5 V	I _C = 0.1 A	(see Notes 3 and 4)		35		
V _{CE(sat)}	Collector-emitter saturation voltage	I _B = I _B =	0.03 A 0.2 A	$I_C = 0.3 A$ $I_C = 1 A$	(see Notes 3 and 4)			0.8 1	V
V _{BE(sat)}	Base-emitter saturation voltage	I _B =	0.2 A	I _C = 1 A	(see Notes 3 and 4)			1.1	V
f _t	Current gain bandwidth product	V _{CE} =	10 V	I _C = 0.2 A			12		MHz
C _{ob}	Output capacitance	V _{CB} =	20 V	I _E = 0	f = 0.1 MHz		60		pF

NOTES: 2. Inductive loop switching measurement.

- 3. These parameters must be measured using pulse techniques, $t_p = 300 \mu s$, duty cycle $\leq 2\%$.
- 4. These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.
- 5. To obtain f_t the $[h_{FE}]$ response is extrapolated at the rate of -6 dB per octave from $f_t = 1$. MHz to the frequency at which $[h_{FE}] = 1$.

thermal characteristics

	PARAMETER			1		MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance	1						2.5	°C/W

resistive-load-switching characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TEST CONDITIONS †		MIN	TYP	MAX	UNIT
t _{on}	Turn on time	To = 1 A	I _{B(on)} = 0.2 A	I _{B(off)} = -0.4 A		0.25	0.5	μs
t _s	Storage time	$I_{C} = 1 \text{ A}$ $V_{CC} = 250 \text{ V}$	(see Figures 1 and 2)	IB(off) = -0.4 A		1.8		μs
t _f	Fall time		(See Figures Faria 2)			0.2		μs
t _f	Fall time	I _C = 1 A V _{CC} = 250 V	$I_{B(on)} = 0.2 \text{ A}$ $T_{C} = 95^{\circ}\text{C}$	$I_{B(off)} = -0.4 A$			0.4	μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.

PARAMETER MEASUREMENT INFORMATION

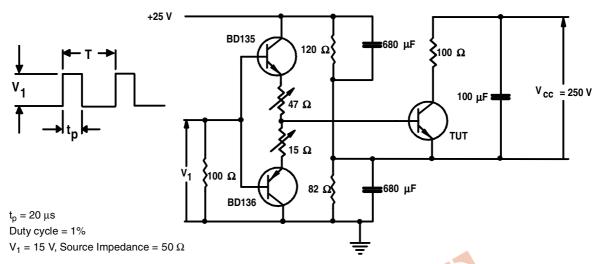


Figure 1. Resistive-Load Switching Test Circuit

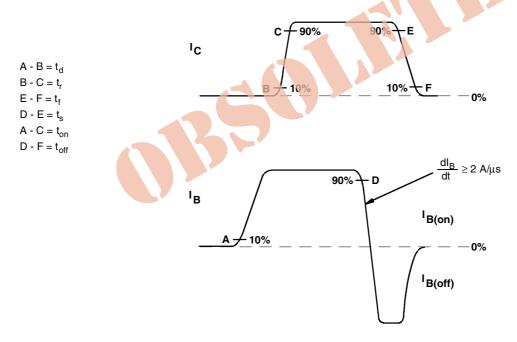
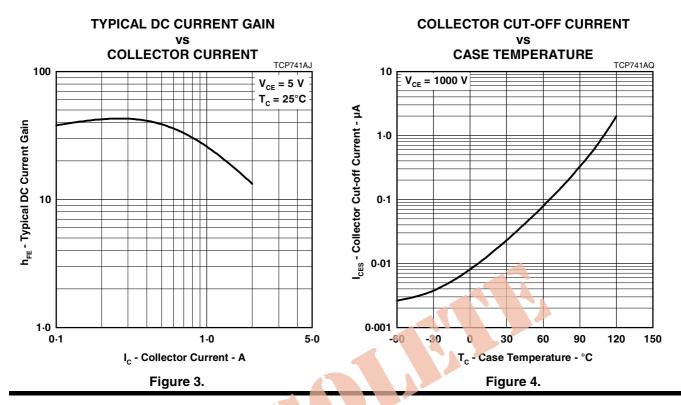


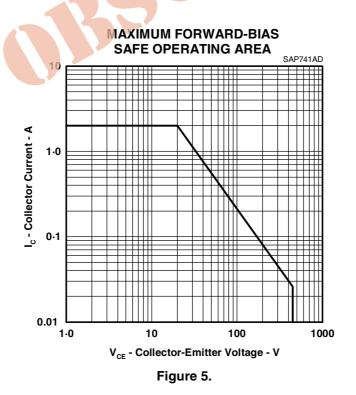
Figure 2. Resistive-Load Switching Waveforms



TYPICAL CHARACTERISTICS



MAXIMUM SAFE OPERATING REGIONS



THERMAL INFORMATION

THERMAL RESPONSE JUNCTION TO CASE

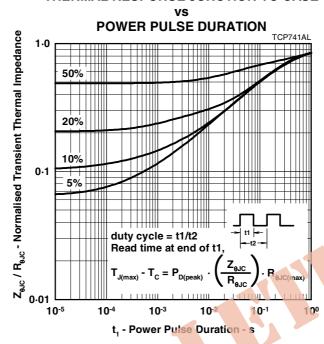


Figure 6